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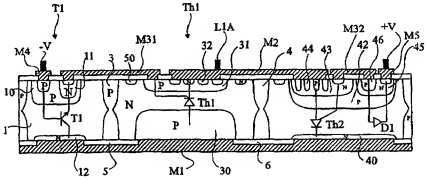

(57) **Abstract**

The invention concerns a monolithic component for protecting a line against surge voltages higher than a predetermined positive threshold or lower than a predetermined negative threshold, comprising in antiparallel a thyristor with cathode gate (TH1) and a thyristor with anode gate (Th1), the gate of the thyristor with cathode gate being connected to a negative voltage threshold (–V) via a transistor amplifying gate current (T1), the gate of the thyristor with anode gate being connected to a positive voltage threshold (+V). The monolithic component is produced in a substrate divided into boxes separated by insulating walls (3, 4) whereof the lower faces are coated with insulating layers (5, 6), the substrate lower face being evenly coated with a metal coating (M1).

SUBSCRIBER INTERFACE PROTECTION CIRCUIT

Abstract

The present invention relates to a monolithic component of protection of a line against overvoltages . than a determined positive threshold or smaller than a determined negative threshold, including in antiparallel a cathode-gate thyristor (Th1) and an anode-gate thyristor (Th2), the gate of the cathode-gate thyristor being connected to a negative threshold voltage (-V) via a gate current amplification transistor (T1), the gate of the anode-gate thyristor being connected to a positive threshold voltage (+V). The monolithic component is made in a substrate divided into wells separated by isolating walls (3, 4), the smaller surfaces of which are coated with insulating layers (5, 6), the smaller surface of the substrate being uniformly coated with a metallization (M1).

Fig. 4B.